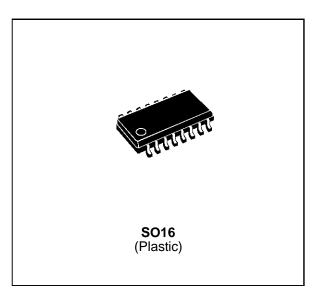


Application Specific Discretes $A.S.D.^{TM}$

IGNITION CONTROL CIRCUIT

FEATURES AND BENEFITS

- MONOLITHIC CIRCUIT FOR CAPACITANCE DISCHARGE SYSTEM CONTROL.
- DEDICATED THYRISTOR STRUCTURE FOR IGNITION OPERATION.
- APPLICATION SPECIFIC DISCRETES (ASDTM).
- SURFACE AREA REDUCTION.
- SO16 PACKAGE.



DESCRIPTION

The ICC01 is a high-performance planar-diffused technology adapted to rugged environment conditions.

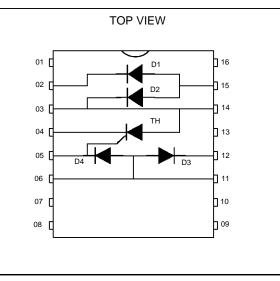
It has been developed especially for small engines using a capacitor discharge technique for ignition operation.

The ICC01 assumes electronics control of the ignition system.

- Pin 2 : Motor stop
- Pin 4/6/11 : Ground
- Pin 5 : Sensor
- Pin 3/14 : Ignition capacitor
- Pin 12/15 : Charging, winding
- Pin 1/7/8/9/10/13/16: Not connected

See basic application and functionality page 4.

FUNCTIONAL DIAGRAM



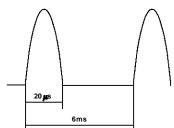
ABSOLUTE MAXIMUM RATINGS : THYRISTOR TH

Symbol	Parameter	Value	Unit	
I _{TRM}	Repetitive peak on-state current (Note1)	TI=110 °C	100	А
ITSM			150	А
Tj initial = T _j = 25° C		tp = 10 ms	5	А
Vdrm	Repetitive peak off-state voltage	T _j = 125°C	400	V

ABSOLUTE MAXIMUM RATINGS : DIODES

Symbol	Parameter			Value			
Symbol				D2	D3	D4	Unit
I _{FRM}	Repetitive peak forward current (Note 1)	TI= 110 °C	1	100	100	1	А
I _{FSM}	Non repetitive surge forward current	tp = 20 μs	15	150	150	15	А
	Tj initial = Tj = 25°Ĉ	tp = 10 ms	2	5	5	2	А
Vrrm	Repetitive peak off-state voltage	Tj= 125 °C	25	400	400	25	V

Note 1: Test current waveform



ABSOLUTE MAXIMUM RATINGS : FOR ALL DEVICES (ICC01)

Symbol	Parameter	Value	Unit
T _{stg} Tj	Storage temperature range Operating junction temperature range	- 40 to + 150 - 40 to + 150	°C
ТІ	Maximum lead temperature for soldering during 10s	260	°C

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth(j-a)	Thermal resistance junction to ambient	90	°C/W



ELECTRICAL CHARACTERISTICS : THYRISTOR TH

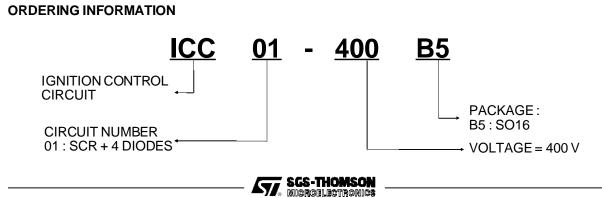
Symbol	Test Conditions		Value	Unit	
I _{GT}	V_D =12V (DC) R _L =33 Ω	Tj= 25°C	MAX	1	mA
V _{GT}	$V_D=12V$ (DC) $R_L=33\Omega$	Tj= 25°C	MAX	1.5	V
V _{TM}	$I_{TM} = 4A$ tp $\leq 1ms$	Tj= 25°C	MAX	1.9	V
I _{DRM}	V _{DRM} rated	Tj= 25°C	MAX	50	μΑ
		Tj= 125°C	MAX	1	mA

ELECTRICAL CHARACTERISTICS : DIODE D1/D4

Symbol	Test Conditions			Value	Unit
I _R	$VR = V_{RRM}$	Tj= 25°C	MAX	50	μΑ
		Tj= 120°C	MAX	1	mA
VF	$I_F = 100 \text{ mA} \text{ tp} \le 1 \text{ ms}$	Tj= 25°C	MAX	1.2	V

ELECTRICAL CHARACTERISTICS : DIODE D2/D3

Symbol	Symbol Test Conditions		Value	Unit	
I _R	$V_{R} = V_{RRM}$	Tj= 25°C	MAX	50	μΑ
		Tj= 125°C	MAX	1	mA
VF	$I_F = 4 A$ tp $\leq 1 ms$	Tj= 25°C	MAX	1.9	V



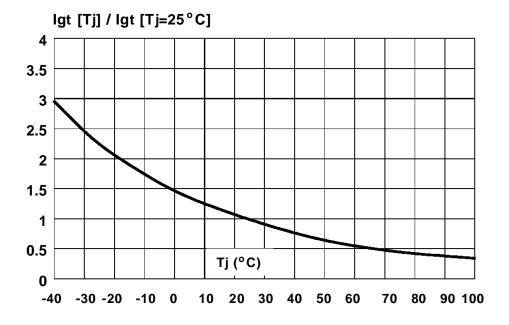
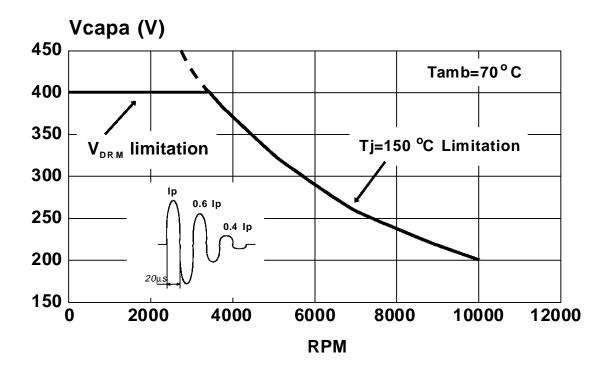


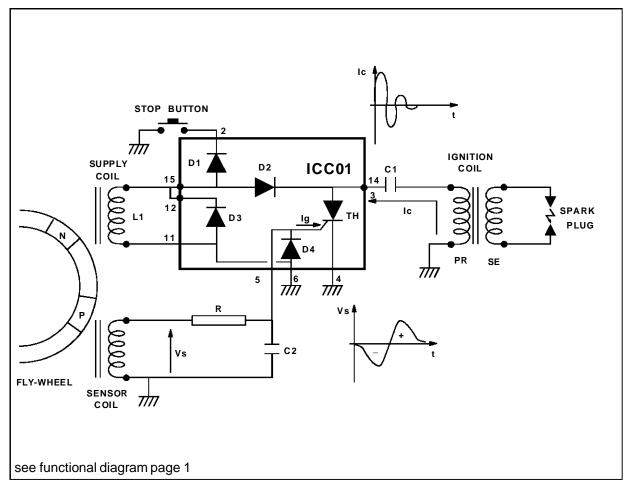
Fig.1 : Relative variation of gate trigger current versus junction temperature.

Fig.2 : Safety limitation curve of the capacitor voltage variation versus RPM @ tp=20µs.





BASIC APPLICATION



The applications using the capacitive ignition system (CDI) operate in 3 phases.

PHASE 1

Storage of the energy in the capacitor C1

PHASE 2

Discharge of the capacitor C1 and spark generation to the ignition coil.

PHASE 3

Engine stop.

1) ENERGY STORAGE IN C1

The coil L1 generates an alternative voltage. Its positive part charges the capacitor C1 through the diode D2.

The negative waves are clamped by the diode D3.

2) SPARK GENERATION

For each fly-wheel revolution the sensor coil produces a bidirectional pulse Vs and triggers the ignition coil.

The negative sinewave generated is clamped by D4 while the positive sinewave initiates a current I_G through the thyristor gate (Th)

The firing of the SCR causes an alternating discharge current Ic through the capacitor C1.

The positive parts of this current flow in the loop C1, Th and the primary of the ignition coil PR.

The negative parts flow through C1, PR and both diodes D3 and D2.

3) ENGINE STOP

The engine stop is obtained by short circuiting the supply coil L1 (stop button). The diode D1 avoids the accidental connection of battery voltage.



R RESISTOR CALCULATION

The purpose of the resistor R is to limit the current I_G through the thyristor gate. Its maximum value can be calculated as follow : R max = (Vs min - V_{GT} max) / 2 I_{GT} max

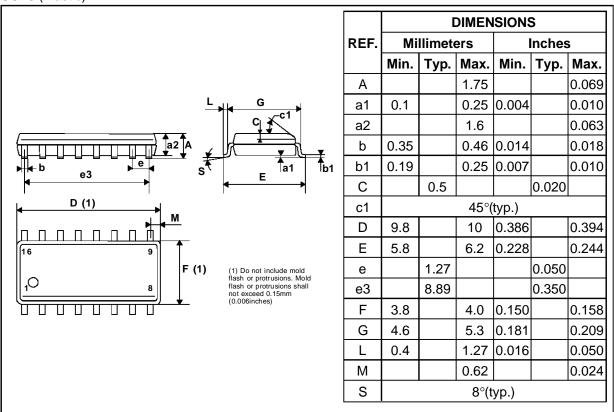
POWER LOSSES (For 20µs - see note 1)

The following equations can be used to evaluate power losses :

 $\begin{array}{lll} \mbox{For TH} & \mbox{V}_{TO} = 2.65 \mbox{V} & \mbox{Rt} = 0.110 \ \Omega \\ \mbox{For D3} & \mbox{V}_{FO} = 1.73 \mbox{V} & \mbox{Rd} = 0.075 \ \Omega \end{array}$

PACKAGE MECHANICAL DATA

SO16 (Plastic)



Marking : ICC1-400 Weight : 0.15 g

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsability for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics or systems without express written approval of SGS-THOMSON Microelectronics.

© 1994 SGS-THOMSON Microelectronics - All rights reserved.

Purchase of I²C Components by SGS-THOMSON Microelectronics, conveys a license under the Philips I²C Patent. Rights to use these components in an I²C system, is granted provided that the system conforms to the I²C Standard Specifications as defined by Philips.

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands Singapore - Spain -Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A.



PROTECTION AGAINST PARASITIC SPIKES

The capacitor C2 in relation with R acts as a filter and avoids the unexpected firing of the thyristor due to parasitic spikes. Good results have been obtained with 10nF capacitance.